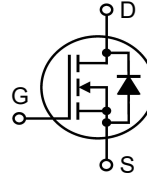


X3-Class HiPerFET™ Power MOSFET

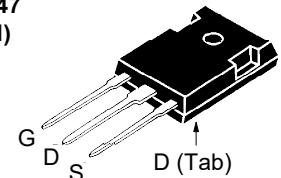
IXFH90N65X3

V_{DSS} = 650V
I_{D25} = 90A
R_{DS(on)} ≤ 33mΩ

N-Channel Enhancement Mode
Avalanche Rated



TO-247
(IXFH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	650	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	650	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	90	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	150	A
I _A	T _C = 25°C	20	A
E _{AS}	T _C = 25°C	3	J
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	50	V/ns
P _D	T _C = 25°C	960	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	°C
M _d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		6	g

Features

- International Standard Package
- Low R_{DS(ON)} and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 1mA	650		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4mA	3.2		5.2 V
I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C			50 μA 6 mA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1			33 mΩ

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	V _{DS} = 10V, I _D = 0.5 • I _{D25} , Note 1	38	65	S
R_{Gi}	Gate Input Resistance		1.5	Ω
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		6080	pF
C_{oss}			8020	pF
C_{rss}			40	pF
Effective Output Capacitance				
C_{o(er)}	Energy related	V _{GS} = 0V V _{DS} = 0.8 • V _{DSS}	270	pF
C_{o(tr)}	Time related		1300	pF
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 2Ω (External)		28	ns
t_r			11	ns
t_{d(off)}			63	ns
t_f			10	ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		95	nC
Q_{gs}			31	nC
Q_{gd}			31	nC
R_{thJC}			0.21	0.13 °C/W
R_{thCS}				°C/W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			90 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			360 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 45\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		175	ns
Q_{RM}			1.3	μC
I_{RM}			15.0	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

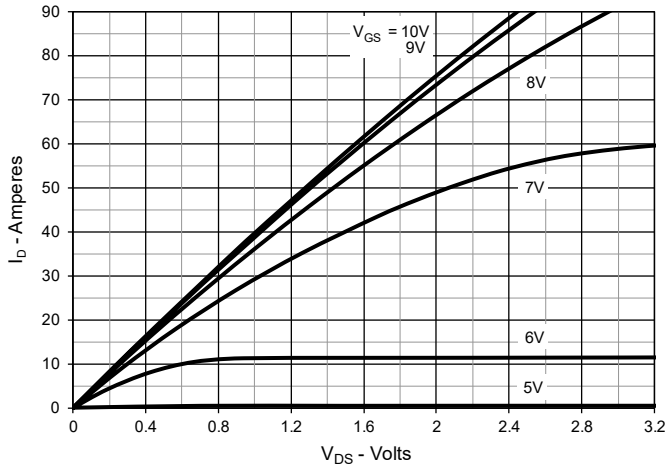
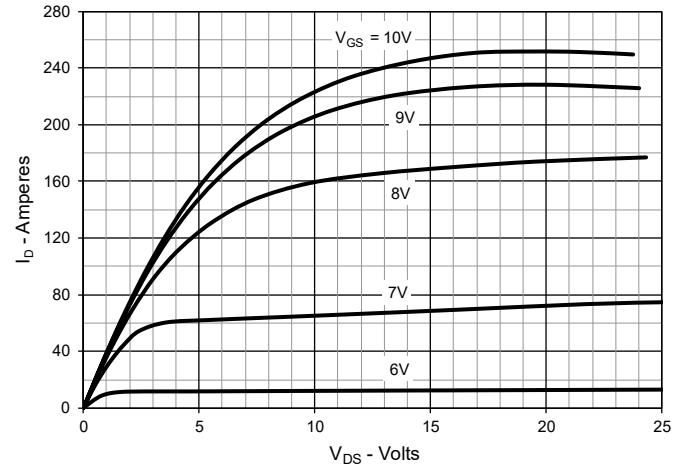
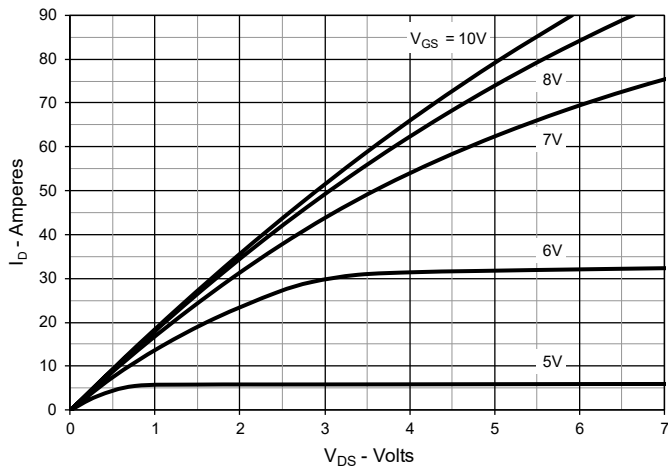
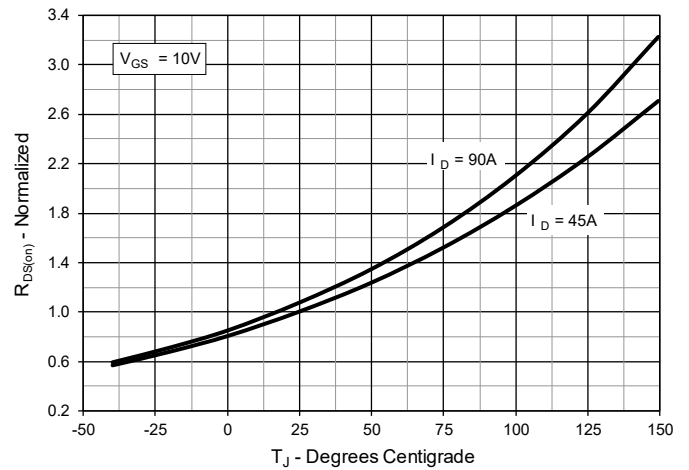
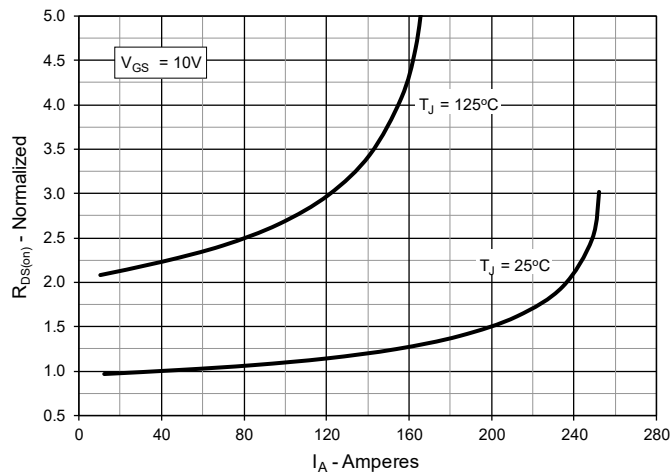
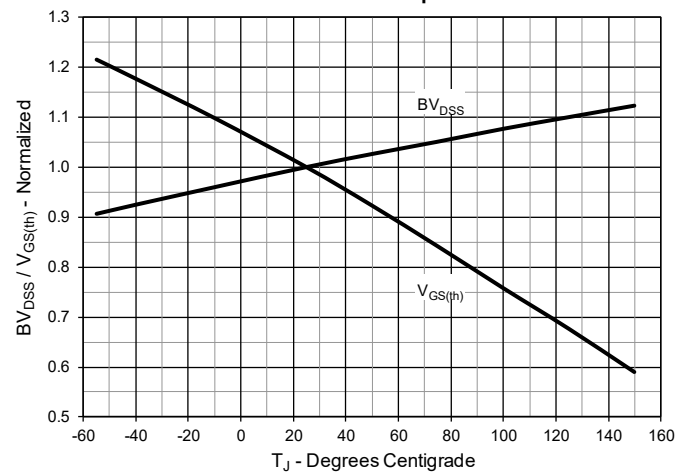
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 45\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 45\text{A}$ Value vs. Drain Current

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature


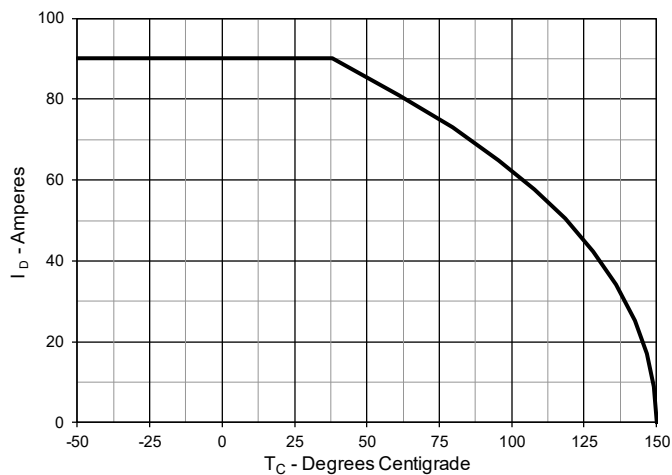
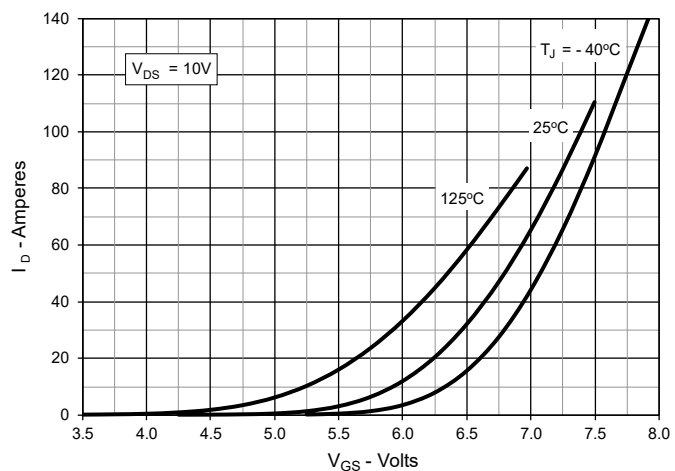
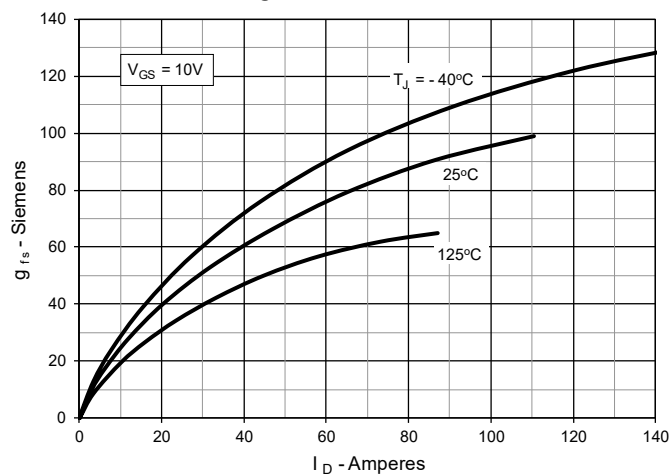
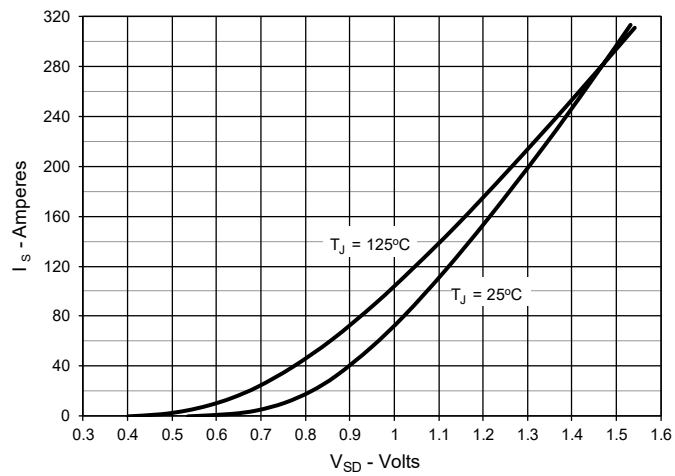
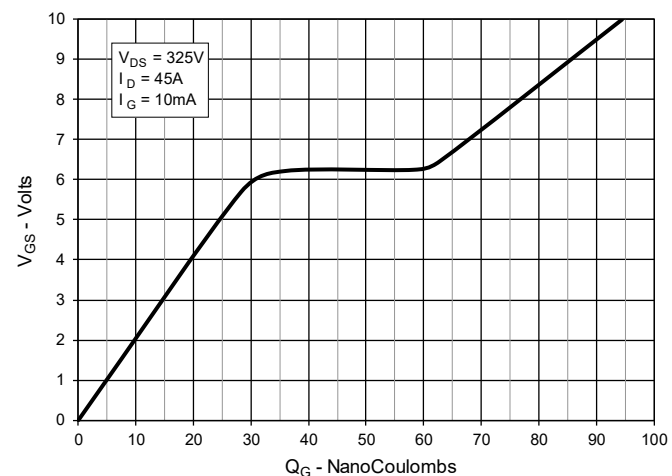
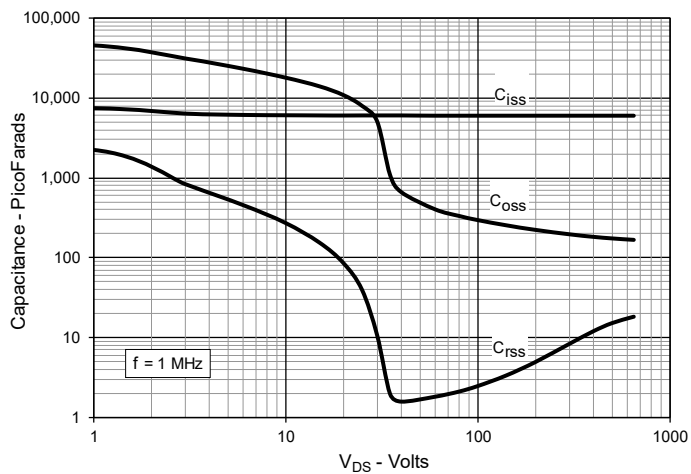
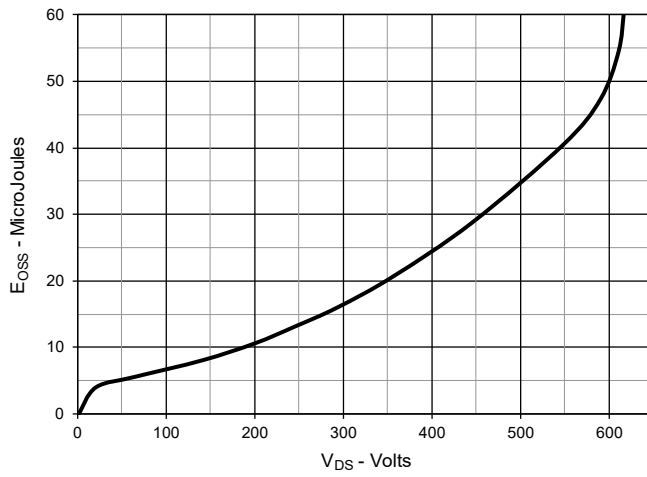
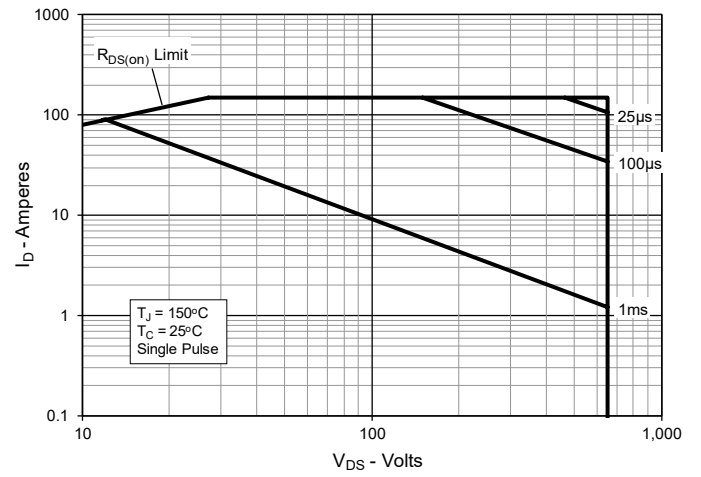
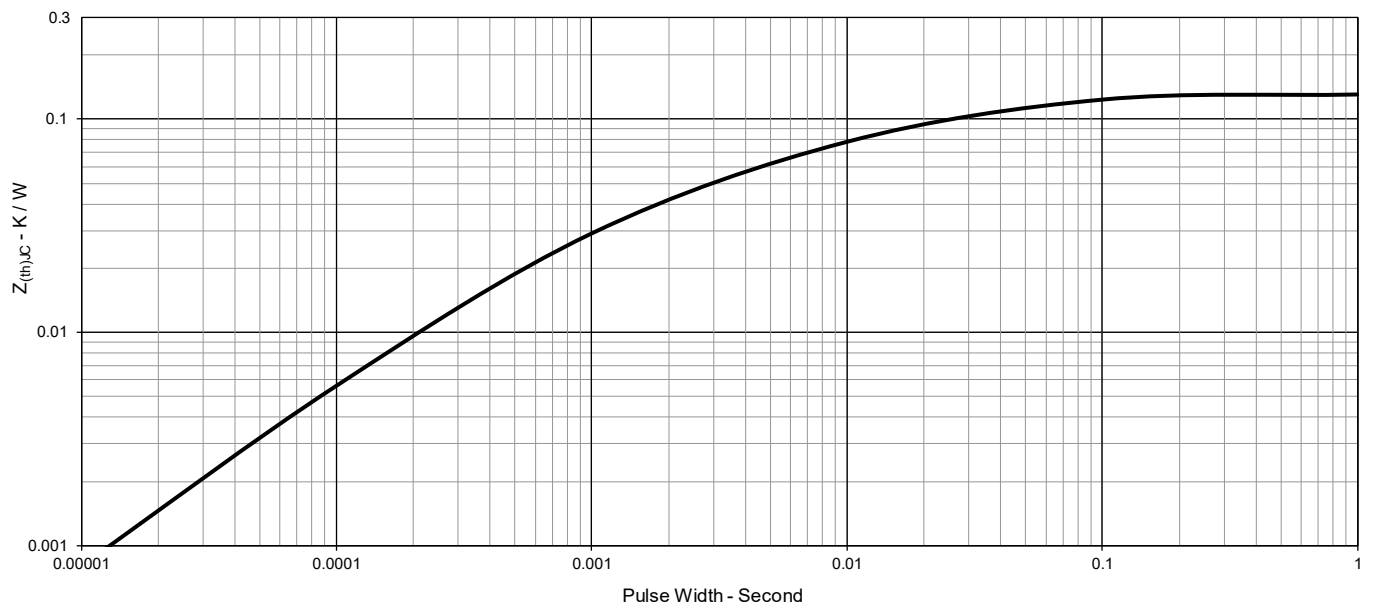
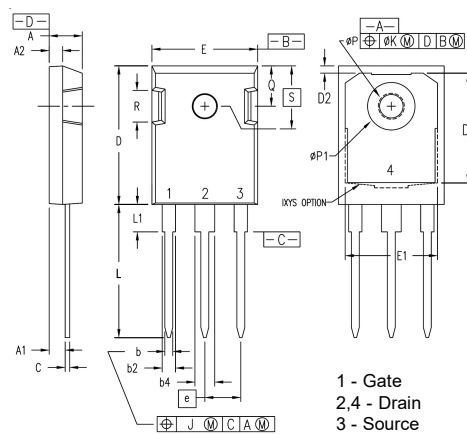
Fig. 7. Maximum Drain Current vs. Case Temperature

Fig. 8. Input Admittance

Fig. 9. Transconductance

Fig. 10. Forward Voltage Drop of Intrinsic Diode

Fig. 11. Gate Charge

Fig. 12. Capacitance


Fig. 13. Output Capacitance Stored Energy

Fig. 14. Forward-Bias Safe Operating Area

Fig. 15. Maximum Transient Thermal Impedance


TO-247 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
ØP	.140	.144	3.55	3.65
ØP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	